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- (54) Title: CRUCIBLE AND METHOD FOR THE PRODUCTION OF A (NEAR) MONOCRYSTALLINE SEMICONDUCTOR INGOT

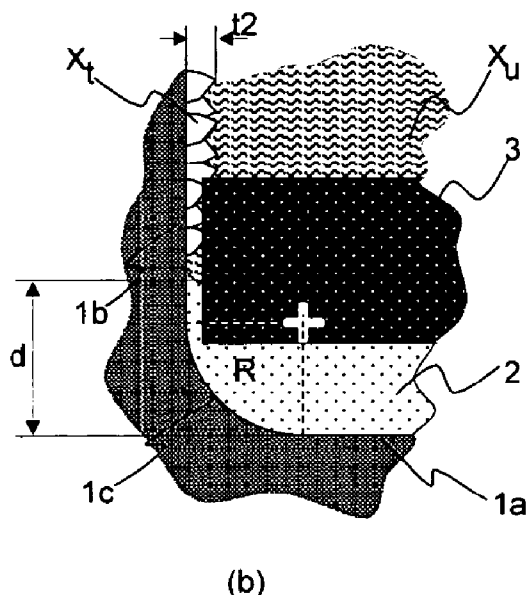


FIGURE 3

- (57) Abstract: The present invention concerns a crucible (1) for the production of crystalline semiconducting material ingots, such as silicon, said crucible comprising peripheral side walls (1b) and a floor (1a) at least a portion of said floor being coated with a top layer (2), characterized in that, said top layer (2) has a thickness, δ , of at least 500 μm and in that, at a deformation temperature below 1400 °C said top layer is plastically or viscously deformable.

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